May 2018





30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | RDS(ON) max | I _D T _A = +25°C |
|-------------------|--------------------------------|--|
| -30V | 75mΩ @ V_{GS} = -10 V | -3.9A |
| | 98mΩ @ V _{GS} = -4.5V | -3.3A |

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

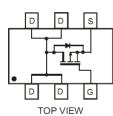
- DC-DC Converters
- **Power Management Functions**
- Backlighting
- Motor Control

Mechanical Data

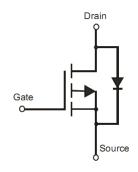
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.013 grams (Approximate)







Internal Schematic



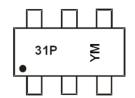
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|--------------|--------|-------------------|
| DMP3105LVT-7 | TSOT26 | 3,000/Tape & Reel |

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



31P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018)M = Month (ex: 9 = September)

Date Code Key

| Year | 2017 | 2018 | 20 | 019 | 2020 | 2021 | | 2 | 2022 | 2023 | 202 | 24 | 2025 |
|-------|------|------|-----|-----|------|------|----|----|------|------|-----|-----|------|
| Code | E | F | | G | Н | I | | | J | K | L | | М |
| Month | Jan | Feb | Mar | Apr | May | Jun | Ju | ul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------|--|------------------|--------------|---|
| Drain-Source Voltage | V_{DSS} | -30 | V | | |
| Gate-Source Voltage | | | V _{GSS} | ±12 | V |
| Continuous Drain Current (Note 5) V _{GS} = -10V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | -3.1 -2.5 | А |
| Continuous Drain Current (Note 5) V _{GS} = -4.5V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | -2.7 -2.2 | А |
| Continuous Drain Current (Note 6) V _{GS} = -10V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | -3.9 -3.1 | А |
| Continuous Drain Current (Note 6) V _{GS} = -4.5V | I _D | -3.3 -2.7 | А | | |
| Maximum Continuous Body Diode Forward Current | Is | -2.2 | Α | | |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | -20 | Α | | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | P_{D} | 1.15 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{	heta JA}$ | 108 | °C/W |
| Total Power Dissipation (Note 6) | P_{D} | 1.75 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{	heta JA}$ | 72 | °C/W |
| Thermal Resistance, Junction to Case (Note 6) | $R_{	heta JC}$ | 23.4 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

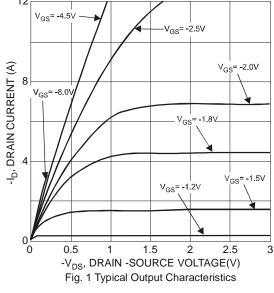
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

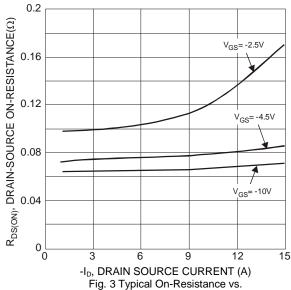
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | | |
|--|---------------------|------|------|------|------|--|--|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -30 | _ | | V | $V_{GS} = 0V, I_D = -250\mu A$ | | |
| Zero Gate Voltage Drain Current | IDSS | _ | _ | -100 | nA | $V_{DS} = -30V, V_{GS} = 0V$ | | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 12V, V_{DS} = 0V$ | | |
| ON CHARACTERISTICS (Note 7) | | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -0.5 | -0.9 | -1.5 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | | |
| | | _ | 65 | 75 | | $V_{GS} = -10V, I_D = -4.2A$ | | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 75 | 98 | mΩ | $V_{GS} = -4.5V, I_{D} = -4.0A$ | | |
| | , , | _ | 98 | 150 | | $V_{GS} = -2.5V, I_D = -3.0A$ | | |
| Forward Transfer Admittance | Y _{fs} | _ | 5 | _ | S | $V_{DS} = -15V, I_{D} = -4.0A$ | | |
| Diode Forward Voltage | V_{SD} | _ | -0.7 | -1.0 | V | $V_{GS} = 0V, I_{S} = -1A$ | | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | | |
| Input Capacitance | Ciss | | 839 | | | | | |
| Output Capacitance | Coss | _ | 47 | _ | pF | $V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz | | |
| Reverse Transfer Capacitance | Crss | | 43 | _ | | 1 = 1.0IVII 12 | | |
| Gate Resistance | R_G | _ | 12.3 | _ | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ | | |
| Total Gate Charge (V _{GS} = -4.5V) | Qg | _ | 9.0 | _ | | | | |
| Total Gate Charge (V _{GS} = -10.0V) | Qg | _ | 19.8 | _ | nC | 15)/ 1 400 | | |
| Gate-Source Charge | Q _{gs} | _ | 1.6 | _ | IIC | $V_{DS} = -15V, I_{D} = -4.0A$ | | |
| Gate-Drain Charge | Q _{gd} | _ | 1.1 | _ | | | | |
| Turn-On Delay Time | t _{D(ON)} | _ | 9.7 | _ | | | | |
| Turn-On Rise Time | t _R | | 17.7 | | | $V_{GS} = -10V, V_{DD} = -15V, R_G = 6\Omega,$ | | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 269 | | ns | I _D = -1A | | |
| Turn-Off Fall Time | t _F | _ | 64 | | | | | |

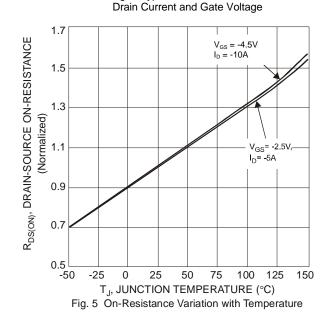
Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.









12 $V_{DS} = -5.0V$ $T_A = 85^{\circ}C$ $T_A = 85^{\circ}C$ $T_A = 150^{\circ}C$ $T_A = 25^{\circ}C$ $T_A = 2$

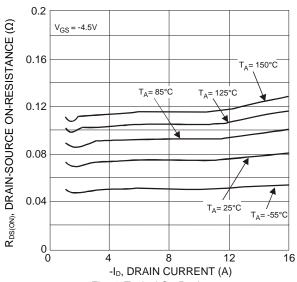


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

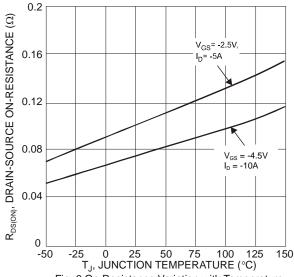
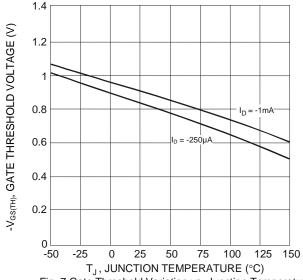
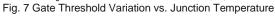


Fig. 6 On-Resistance Variation with Temperature







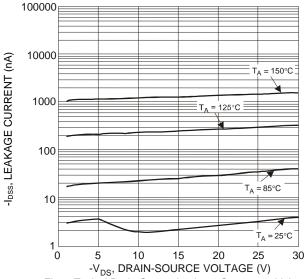


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

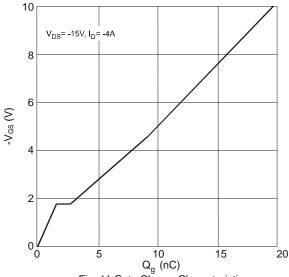
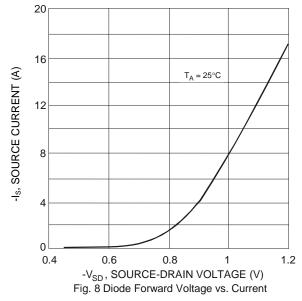
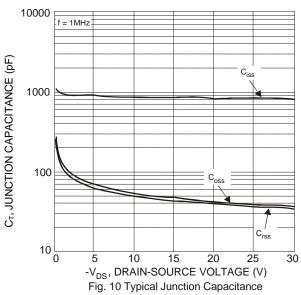
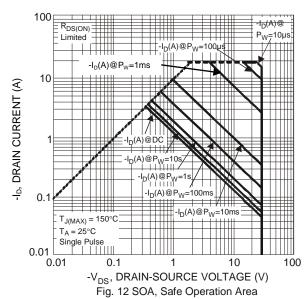


Fig. 11 Gate Charge Characteristics









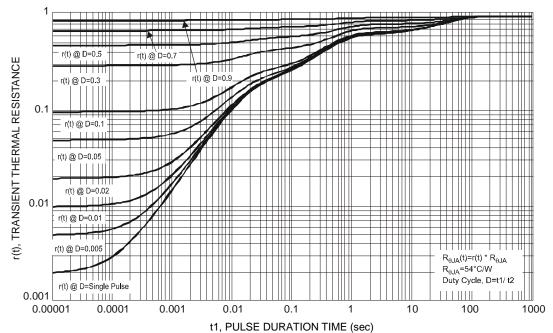


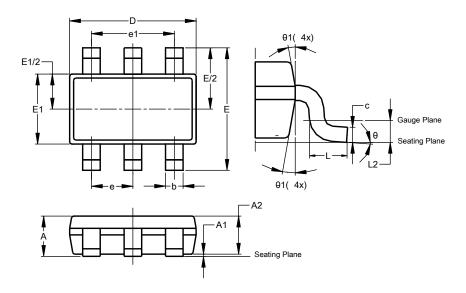
Fig. 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

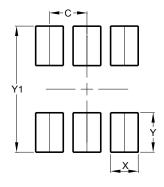


| | TSOT26 | | | | | | |
|-----|----------------------|---------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 1 | 1.00 | - | | | | |
| A1 | 0.010 | 0.100 | - | | | | |
| A2 | 0.840 | 0.900 | _ | | | | |
| D | 2.800 | 3.000 | 2.900 | | | | |
| E | 2 | .800 BS | С | | | | |
| E1 | 1.500 | 1.700 | 1.600 | | | | |
| b | 0.300 | 0.450 | _ | | | | |
| С | 0.120 | 0.200 | - | | | | |
| е | 0.950 BSC | | | | | | |
| e1 | 1.900 BSC | | | | | | |
| L | 0.30 | 0.50 | - | | | | |
| L2 | 0.250 BSC | | | | | | |
| θ | 0° | 8° | 4° | | | | |
| θ1 | 4° 12° – | | - | | | | |
| Α | All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 0.950 |
| Х | 0.700 |
| Y | 1.000 |
| Y1 | 3.199 |



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